
Parameter	Value
Silicon thickness	300 μm
Strip pitch	40–120 μm
Strip width	11–38 μm
Routing line width	$\sim 11 \mu\text{m}$
Inner silicon edge to beam axis	7 mm
Radial distance of active strips from beam axis	8.2–42 mm
Sensor position along beam-axis	–300 to 750 mm
Oxygen enhancement	$> 1 \times 10^{17} \text{ cm}^{-3}$
